

FOCUSSED ION BEAM VISUAL ENDPOINTING

ABSTRACT

A method for use in removing a portion of a semiconductor chip. The method comprises etching a backside of the semiconductor chip, the frontside including a first well with a first type of doping and a second well with a second type of doping; monitoring a backside of the semiconductor chip during etching; and determining when a first portion of the backside over one of the first and second wells differs from a second portion of the backside over the other of the first and second wells. A method for etch endpoint detection includes etching a backside of a semiconductor chip, the semiconductor chip having at least one doped well formed proximate a frontside of the semiconductor chip; monitoring the backside of the semiconductor chip during etching until at least one doped well becomes visible; and stopping etching after the doped well becoming visible.